



John Bravman

Bing Centennial Prof, Freeman-Thornton Chair for Vice Provost for Undergrad Ed, & Dean of Fresh-Soph College, & Prof of Materials Sci & Eng, Emeritus
Materials Science and Engineering

Bio

BIO

<https://www.bucknell.edu/meet-bucknell/bucknell-leadership/meet-president-bravman>

ACADEMIC APPOINTMENTS

- Emeritus Faculty, Acad Council, Materials Science and Engineering
- Member, Cardiovascular Institute

ADMINISTRATIVE APPOINTMENTS

- President, Bucknell University, (2010- present)

Publications

PUBLICATIONS

- **Stress relaxation in free-standing aluminum beams** *THIN SOLID FILMS*
Lee, H. J., Zhang, P., Bravman, J. C.
2005; 476 (1): 118-124
- **White beam analysis of coupling between precipitation and plastic deformation during electromigration in a passivated Al(0.5wt.% Cu) interconnect** *METALLOFIZIKA I NOVEISHIE TEKHNologii*
Barabash, R. I., Ice, G. E., Tamura, N., Valek, B. C., Bravman, J. C., Patel, J. R.
2005; 27 (1): 75-94
- **Quantitative characterization of electromigration-induced plastic deformation in Al(0.5wt%Cu) interconnect** *Symposium on Characterization and Mechanical Reliability of Advanced Electronic Materials at Nanoscale*
Barabash, R. I., Ice, G. E., Tamura, N., Valek, B. C., Bravman, J. C., Spolenak, R., Patel, J. R.
ELSEVIER SCIENCE BV.2004: 24-30
- **Study on the strength and elongation of free-standing Al beams for microelectromechanical systems applications** *APPLIED PHYSICS LETTERS*
Lee, H. J., Zhang, P., Bravman, J. C.
2004; 84 (6): 915-917
- **Important factors for silane adhesion promoter efficacy: surface coverage, functionality and chain length** *JOURNAL OF ADHESION SCIENCE AND TECHNOLOGY*
JENKINS, M. L., Dauskardt, R. H., Bravman, J. C.
2004; 18 (13): 1497-1516
- **Quantitative analysis of dislocation arrangements induced by electromigration in a passivated Al (0.5 wt % Cu) interconnect** *JOURNAL OF APPLIED PHYSICS*
Barabash, R. I., Ice, G. E., Tamura, N., Valek, B. C., Bravman, J. C., Spolenak, R., Patel, J. R.

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- **Scanning X-ray microdiffraction with submicrometer white beam for strain/stress and orientation mapping in thin films** *JOURNAL OF SYNCHROTRON RADIATION*
Tamura, N., MacDowell, A. A., Spolenak, R., Valek, B. C., Bravman, J. C., Brown, W. L., Celestre, R. S., Padmore, H. A., Batterman, B. W., Patel, J. R.
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- **Tensile failure by grain thinning in micromachined aluminum thin films** *JOURNAL OF APPLIED PHYSICS*
Lee, H. J., Zhang, P., Bravman, J. C.
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- **Electromigration-induced plastic deformation in passivated metal lines** *APPLIED PHYSICS LETTERS*
Valek, B. C., Bravman, J. C., Tamura, N., MacDowell, A. A., Celestre, R. S., Padmore, H. A., Spolenak, R., Brown, W. L., Batterman, B. W., Patel, J. R.
2002; 81 (22): 4168-4170
- **Effect of interface conditions on yield behavior of passivated copper thin films** *JOURNAL OF MATERIALS RESEARCH*
Vinci, R. P., Forrest, S. A., Bravman, J. C.
2002; 17 (7): 1863-1870
- **Subcritical debonding of polymer/silica interfaces under monotonic and cyclic loading** *Symposium on Computational Thermodynamics and Materials Design*
Snodgrass, J. M., Pantelidis, D., JENKINS, M. L., Bravman, J. C., Dauskardt, R. H.
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- **Mechanical tests of free-standing aluminum microbeams for MEMS application** *Symposium on Mechanical Properties of Structural Films*
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- **Differential thermal budget in laser processing: Application to formation of titanium silicide** *IEEE ELECTRON DEVICE LETTERS*
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- **A high-voltage scanning electron microscopy system for in situ electromigration testing** *REVIEW OF SCIENTIFIC INSTRUMENTS*
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- **Effect of microstructure and chemical bonding on the adhesion strength of a silicon/polymer interface for microelectronic packaging applications** *Symposium D on Integration of Dissimilar Materials in Micro- and Optoelectronics / Symposium I on III-V and SiGe Group IV Device/IC Processing Challenges for Commercial Applications, at the 1998 MRS Fall Meeting*
Pantelidis, D., Lee, H. J., Bravman, J. C.
MATERIALS RESEARCH SOCIETY.1999: 165–170
- **Stress-induced and electromigration voiding in nitride passivated Al interconnects** *5th International Workshop on Stress Induced Phenomena in Metallization*
Lee, S. H., Lee, S., Bravman, J. C., Flinn, P. A., Marieb, T. N.
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- **The effects of passivation thickness and initial aluminum line stress on electromigration behavior** *Symposium on Materials Reliability in Microelectronics VIII*
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Lim, H. J., DeMattei, R. C., Feigelson, R. S.
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- **Determination of temperature dependent unstressed lattice spacings in crystalline thin films on substrates** *Symposium on Thin-Films - Stresses and Mechanical Properties VII at the MRS Fall Meeting*
Cornella, G., Lee, S., Kraft, O., Nix, W. D., Bravman, J. C.
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- **High voltage scanning electron microscopy for in-situ electromigration studies** *14th International Congress on Electron Microscopy*
Bravman, J. C., Flinn, P. A., Marieb, T. N., Lee, S., Doan, J.
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- **Void phenomena in passivated metal lines: Recent observations and interpretation** *4th International Workshop on Stress Induced Phenomena in Metallization*
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Lee, S., Doan, J., Bravman, J. C., Flinn, P. A., Marieb, T. N., Ogawa, S.
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 - **Finite element modeling of grain aspect ratio and strain energy density in a textured copper thin film** *Symposium on Thin Films - Stresses and Mechanical Properties VI, at the 1996 MRS Spring Meeting*
Vinci, R. P., Bravman, J. C.
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 - **Comparison of stresses in Al lines under various passivations** *Symposium on Materials Reliability in Microelectronics, at the 1997 MRS Spring Meeting*
Lee, S., Bravman, J. C., Flinn, P. A., Marieb, T. N.
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 - **Observation of electromigration voiding in Cu lines** *Symposium on Materials Reliability in Microelectronics, at the 1997 MRS Spring Meeting*
Lee, S. H., Bravman, J. C., Flinn, P. A., Arnaud, L.
MATERIALS RESEARCH SOCIETY.1997: 235-239
 - **In-situ measurement of viscous flow of thermal silicon dioxide thin films at high temperature** *Symposium on Amorphous and Crystalline Insulating Thin Films, at the 1996 MRS Fall Meeting*
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 - **Stress and microstructural evolution of LPCVD polysilicon thin films during high temperature annealing** *Symposium on Thin Films - Structure and Morphology*
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 - **PHASE-EQUILIBRIA IN THE Y-BA-CU-O SYSTEM AND MELT PROCESSING OF AG CLAD Y1BA2CU3O7-X TAPES AT REDUCED OXYGEN PARTIAL PRESSURES** *PHYSICA C-SUPERCONDUCTIVITY AND ITS APPLICATIONS*
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ZIELINSKI, E. M., Vinci, R. P., Bravman, J. C.
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 - **A simple analysis of average mechanical behaviour and strain energy density of misoriented grains in a textured film** *5th Symposium on Materials Reliability in Microelectronics, at the 1995 MRS Spring Meeting*
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- **PHASE-EQUILIBRIA AND MELT PROCESSING OF $\text{Bi}_2\text{Sr}_2\text{Ca}_1\text{Cu}_2\text{O}_{8+x}$ TAPES AT REDUCED OXYGEN PARTIAL PRESSURES** *APPLIED PHYSICS LETTERS*
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- **THERMAL-STRESSES IN PASSIVATED COPPER INTERCONNECTS DETERMINED BY X-RAY-ANALYSIS AND FINITE-ELEMENT MODELING** *4th Symposium on Materials Reliability in Microelectronics, at the 1994 MRS Spring Meeting*
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MATERIALS RESEARCH SOC.1994: 289-294
- **UNDERSTANDING AND ELECTROCHEMICAL CONTROL OF $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$ THIN-FILM EPITAXY ON YTTRIUM STABILIZED ZIRCONIA** *JOURNAL OF APPLIED PHYSICS*

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